

# RJK0348DSP

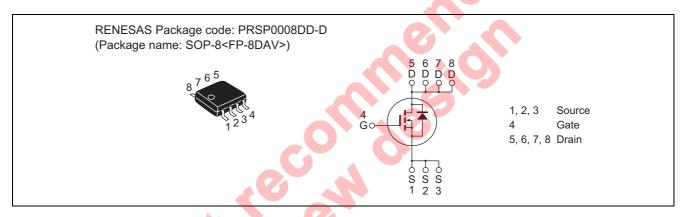
# Silicon N Channel Power MOS FET Power Switching

REJ03G1644-0201 Rev.2.01 Apr 24, 2008

### **Features**

- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance  $R_{DS(on)} = 2.6 \text{ m}\Omega \text{ typ. (at } V_{GS} = 10 \text{ V)}$
- Pb-free

### **Outline**



# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ 

| Item                                   | Symbol                      | Ratings     | Unit |
|----------------------------------------|-----------------------------|-------------|------|
| Drain to source voltage                | $V_{DSS}$                   | 30          | V    |
| Gate to source voltage                 | $V_{GSS}$                   | ±20         | V    |
| Drain current                          | I <sub>D</sub>              | 22          | A    |
| Drain peak current                     | I <sub>D(pulse)</sub> Note1 | 176         | A    |
| Body-drain diode reverse drain current | I <sub>DR</sub>             | 22          | A    |
| Avalanche current                      | I <sub>AP</sub> Note 2      | 22          | A    |
| Avalanche energy                       | E <sub>AR</sub> Note 2      | 48.4        | mJ   |
| Channel dissipation                    | Pch Note3                   | 2.5         | W    |
| Channel to ambient thermal impedance   | θch-a <sup>Note3</sup>      | 50          | °C/W |
| Channel temperature                    | Tch                         | 150         | °C   |
| Storage temperature                    | Tstg                        | -55 to +150 | °C   |

Notes: 1. PW  $\leq$  10  $\mu$ s, duty cycle  $\leq$  1%

- 2. Value at Tch = 25°C, Rg  $\geq$  50  $\Omega$
- 3. When using the glass epoxy board (FR4 40 x 40 x 1.6 mm), PW  $\leq$  10s

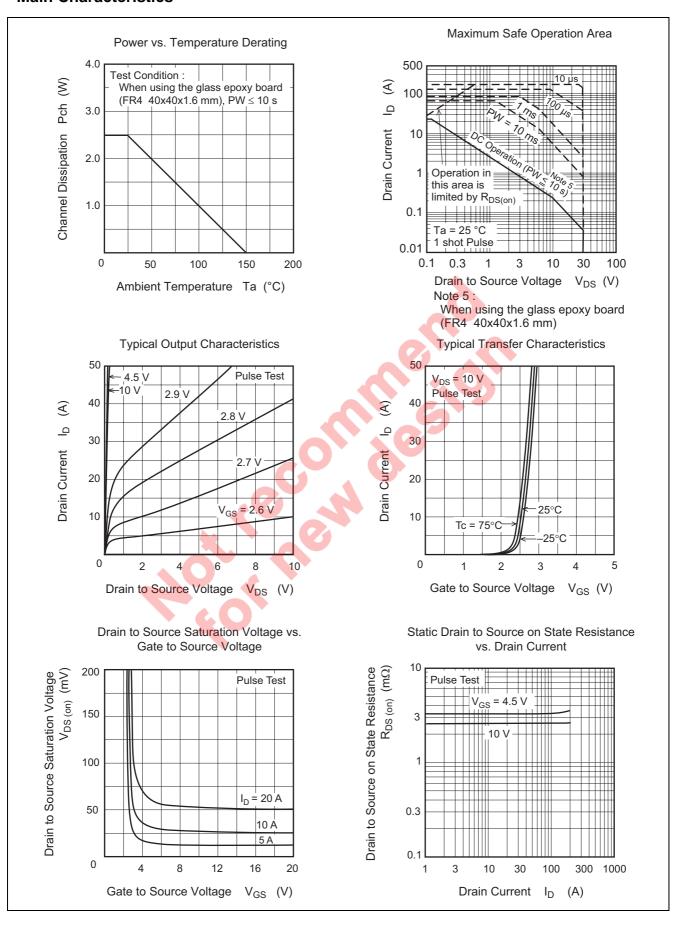
### **Electrical Characteristics**

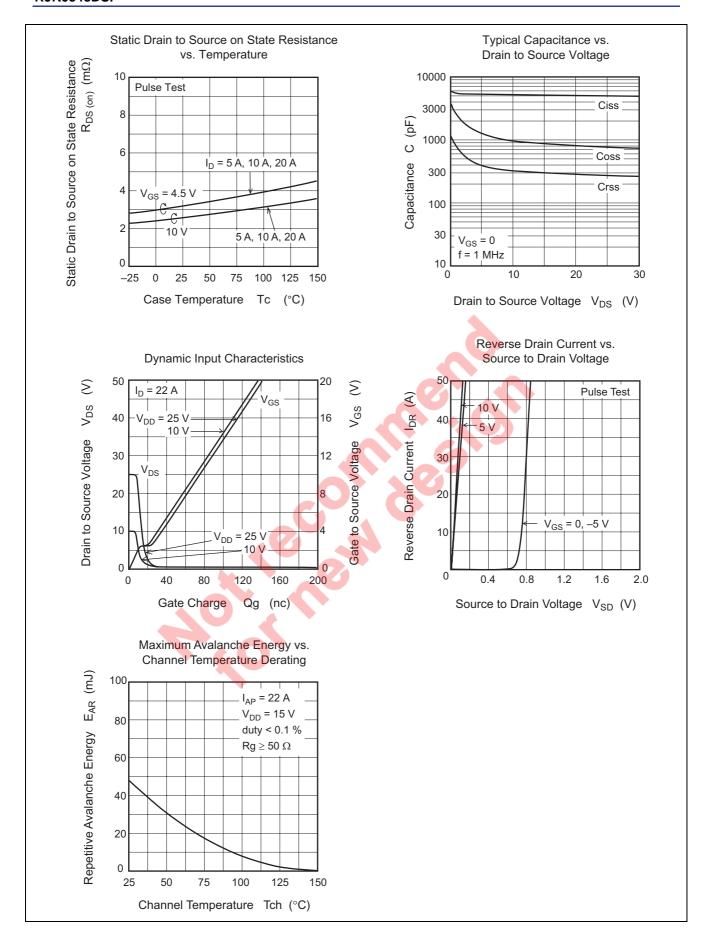
 $(Ta = 25^{\circ}C)$ 

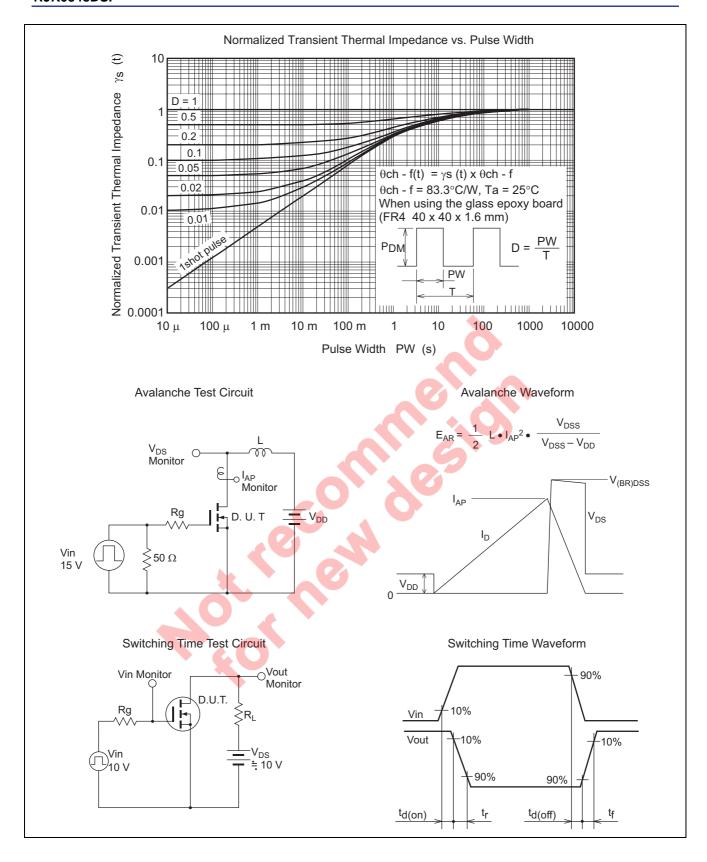
| Item                              | Symbol               | Min | Тур  | Max   | Unit | Test Conditions                                             |
|-----------------------------------|----------------------|-----|------|-------|------|-------------------------------------------------------------|
| Drain to source breakdown voltage | $V_{(BR)DSS}$        | 30  | _    | _     | V    | $I_D = 10 \text{ mA}, V_{GS} = 0$                           |
| Gate to source leak current       | I <sub>GSS</sub>     |     | _    | ± 0.1 | μΑ   | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$                     |
| Zero gate voltage drain current   | I <sub>DSS</sub>     |     | _    | 1     | μΑ   | $V_{DS} = 30 \text{ V}, V_{GS} = 0$                         |
| Gate to source cutoff voltage     | V <sub>GS(off)</sub> | 1.2 | _    | 2.5   | V    | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$                 |
| Static drain to source on state   | R <sub>DS(on)</sub>  |     | 2.6  | 3.4   | mΩ   | $I_D = 11 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$         |
| resistance                        | R <sub>DS(on)</sub>  | _   | 3.2  | 4.5   | mΩ   | $I_D = 11 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$ |
| Forward transfer admittance       | y <sub>fs</sub>      | _   | 60   | _     | S    | $I_D = 11 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$  |
| Input capacitance                 | Ciss                 | 1   | 5100 | 1     | pF   | V <sub>DS</sub> = 10 V                                      |
| Output capacitance                | Coss                 | 1   | 980  | 1     | pF   | $V_{GS} = 0$                                                |
| Reverse transfer capacitance      | Crss                 | _   | 315  | _     | pF   | f = 1 MHz                                                   |
| Gate Resistance                   | Rg                   | _   | 1.4  | _     | Ω    |                                                             |
| Total gate charge                 | Qg                   | _   | 34   | _     | nC   | $V_{DD} = 10 \text{ V}$                                     |
| Gate to source charge             | Qgs                  | _   | 12.5 | _     | nC   | $V_{GS} = 4.5 \text{ V}$                                    |
| Gate to drain charge              | Qgd                  | _   | 7.0  | _     | nC   | I <sub>D</sub> = 22 A                                       |
| Turn-on delay time                | $t_{d(on)}$          | _   | 13   | _     | ns   | $V_{GS} = 10 \text{ V}, I_D = 11 \text{ A}$                 |
| Rise time                         | t <sub>r</sub>       | _   | 5.8  | _ (   | ns   | $V_{DD} \cong 10 \text{ V}$                                 |
| Turn-off delay time               | $t_{\text{d(off)}}$  | _   | 69   |       | ns   | $R_L = 0.91 \Omega$                                         |
| Fall time                         | t <sub>f</sub>       | _   | 10   |       | ns   | $Rg = 4.7 \Omega$                                           |
| Body-drain diode forward voltage  | $V_{DF}$             | _   | 0.78 | 1.02  | V    | $I_F = 22 \text{ A}, V_{GS} = 0^{\text{Note4}}$             |
| Body-drain diode reverse recovery | t <sub>rr</sub>      | _   | 35   | _     | ns   | $I_F = 22 \text{ A}, V_{GS} = 0$                            |
| time                              |                      |     |      |       |      | $di_F/dt = 100 A/ \mu s$                                    |
| Notes: 4. Pulse test              |                      |     |      |       |      |                                                             |

Notes: 4. Pulse test

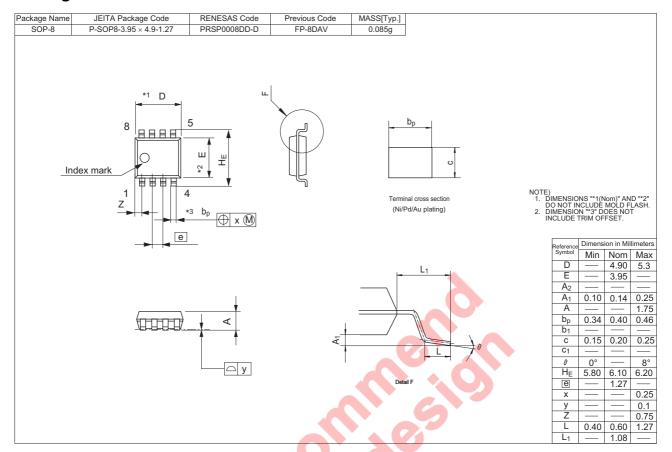
### **Main Characteristics**







### **Package Dimensions**



# **Ordering Information**

| Part No.         | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK0348DSP-00-J0 | 2500 pcs | Taping             |

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